

# UPG30N120

# Insulated Gate Bipolar Transistor

# 1200V SMPS N-CHANNEL IGBT

## DESCRIPTION

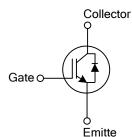
The UTC **UPG30N120** is a N-channel IGBT. it uses UTC's advanced technology to provide customers with high input impedance, high switching speed and low conduction loss, etc.

The UTC **UPG30N120** is suitable for high voltage switching, high frequency switch mode power supplies.

## FEATURES

- \*  $V_{CE(SAT)} \le 2.8V @ I_C=30A, V_{GE}=15V$
- \* 1200V Switching SOA Capability
- \* High switching speed
- \* High input impedance
- \* Low conduction loss

#### SYMBOL

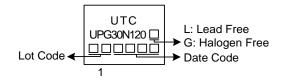


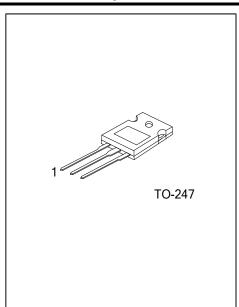
# ORDERING INFORMATION

Ordering	Deekege	Pin Assignment			Dealing		
Lead Free	Halogen Free	Package	1	2	3	Packing	
UPG30N120L-T47-T	UPG30N120G-T47-T	TO-247	G	С	Е	Tube	
Note: Pin Assignment: G: Ga	te C: Collector E: Emit	ter					

(1) T: Tube	
(2)Package Type (2) T47: TO-247	
(3) Green Package (3) G: Halogen Free and Lead Free, L: Lead Free	

## MARKING





PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Emitter Voltage		V <sub>CES</sub>	1200	V
Gate to Emitter Voltage Continuous		V <sub>GES</sub>	±30	V
Continuous Collector Current	T <sub>C</sub> =25°C	Ic	60	А
	T <sub>C</sub> =100°C		30	А
Collector Current Pulsed (Note 2)		I <sub>CM</sub>	100	А
Average Rectified Output Current	T <sub>C</sub> =25°C	I <sub>F</sub>	30	А
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load		I <sub>FSM</sub>	100	A
Single Pulse Avalanche Energy (Note 3)		E <sub>AS</sub>	245	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.2	V/ns
Power Dissipation		PD	350	W
Junction Temperature		TJ	-55 ~ +150	°C
Storage Temperature Range		T <sub>STG</sub>	-55 ~ +150	°C

#### ■ ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub>=25°C, unless otherwise specified)

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3. L=10mH, PK<sub>IL</sub>=7.0A, V<sub>CC</sub>=50V, R<sub>G</sub>=25 $\Omega$ , Starting T<sub>J</sub>=25°C
- 4. I<sub>F</sub>  $\leq$ 25A, di/dt  $\leq$ 200A/µs, V<sub>CC</sub>  $\leq$  BV<sub>CES</sub>, Starting T<sub>J</sub>=25°C

## THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	θյς	0.35	°C/W

## ■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN	TYP	MAX	UNIT
Collector-Emitter Breakdown Voltage	$BV_{CES}$	l <sub>C</sub> =250μA, V <sub>GE</sub> =0V		1200			V
Collector-Emitter Leakage Current	I <sub>CES</sub>	V <sub>CE</sub> =1200V, V <sub>GE</sub> =0V	=1200V, V <sub>GE</sub> =0V			200	μA
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		TJ=25°C		2.0	2.8	V
		I <sub>C</sub> =30A, V <sub>GE</sub> =15V	T <sub>J</sub> =150°C		2.4		V
Gate to Emitter Threshold Voltage	V <sub>GE(TH)</sub>	I <sub>C</sub> =250μA, V <sub>CE</sub> =V <sub>GE</sub>		4.5		6.5	V
Gate to Emitter Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> =0V, V <sub>GE</sub> =15V			±400	nA	
Input Capacitance	CIES	V <sub>CE</sub> =25V, V <sub>GE</sub> =0V, f=1MHz			1990		рF
Output Capacitance	COES				180		pF
Reverse Transfer Capacitance	C <sub>RES</sub>			65		pF	
Total Gate Charge	$Q_{G}$	I <sub>C</sub> =30A, V <sub>CE</sub> =50V, V <sub>GE</sub> =15V			96		nC
Gate-Emitter Charge	$Q_{GE}$				16		nC
Gate-Collector Charge	$Q_{GC}$				54		nC
Current Turn-On Delay Time	t <sub>D(ON)</sub>				80		ns
Current Rise Time	t <sub>R</sub>	I <sub>C</sub> =30A, V <sub>CE</sub> =50V, V <sub>GE</sub> =15V, R <sub>G</sub> =10Ω			145		ns
Current Turn-Off Delay Time	t <sub>D(OFF)</sub>				220		ns
Current Fall Time	t <sub>F</sub>				67		ns
SOURCE- DRAIN DIODE RATINGS AN	ID CHARAC	TERISTICS					
Forward Voltage Drop	V <sub>FM</sub>	I <sub>F</sub> =30A			2.5		V
Reverse Recovery Time	t <sub>rr</sub>				220		ns
Reverse Recovery Charge	Qrr	I <sub>F</sub> =30A, dI/dt=100A/µS			1.2		μC
Note: Pulse Test: Pulse width < 50us	•	-		•	•	•	

Note: Pulse Test: Pulse width  $\leq$  50µs.



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# TEST CIRCUIT AND WAVEFORMS

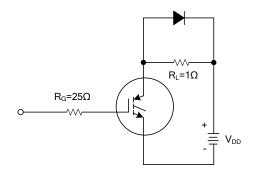


Fig 1. INDUCTIVE SWITCHING TEST CIRCUIT

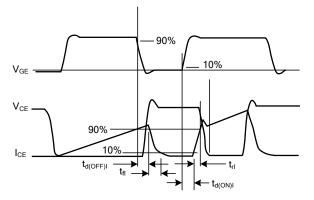
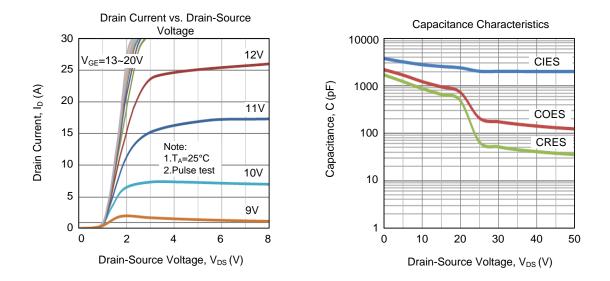


Fig 2. SWITCHING TEST WAVEFORMS



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# TYPICAL CHARACTERISTICS



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